

Product Summary

BV _{bss}	R _{DS(ON)}	I _D T _A = +25°C
50V	1.6Ω @ V _{GS} = 10V	350mA
	2.5Ω @ V _{GS} = 4.5V	200mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

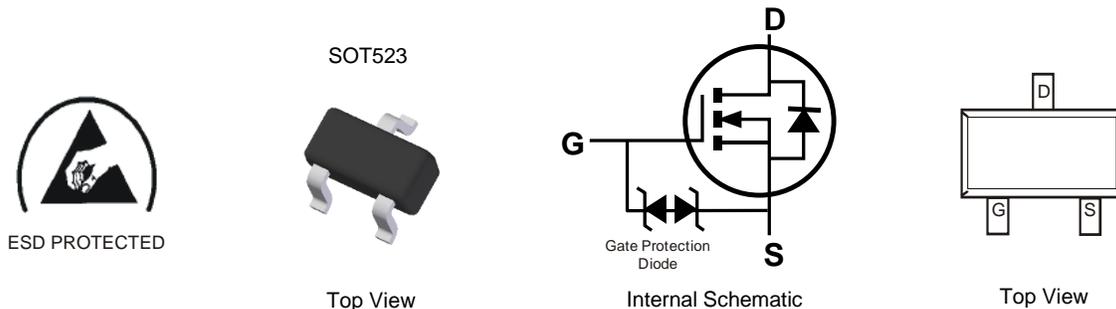
- Motor driving
- Power management functions
- Load switching

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/ Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DIODES™ DMN53D0LTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: SOT523
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

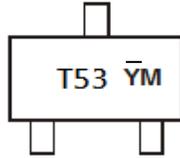


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN53D0LTQ-7	SOT523	3000	Reel
DMN53D0LTQ-13	SOT523	10000	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



T53 = Product Type Marking Code
 ȲM = Date Code Marking
 Ȳ = Year (ex: J = 2022)
 M = Month (ex: 9 = September)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	M	N	O	P	R	S	T	U	V

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	350
		T _A = +70°C	280
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	350	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	1.0	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	420	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout..

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.8	—	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.06	1.6	Ω	V _{GS} = 10V, I _D = 500mA V _{GS} = 4.5V, I _D = 200mA V _{GS} = 2.5V, I _D = 100mA
		—	1.09	2.5		
		—	1.45	4.5		
Source-Drain Diode Forward Voltage	V _{SD}	—	0.88	1.4	V	V _{GS} = 0V, I _S = 500mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iSS}	—	46	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	5.3	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	4.0	—	pF	
Gate Resistance	R _g	—	51	—	Ω	f = 1MHz, V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge (V _{GS} = 10V)	Q _g	—	1.4	—	nC	V _{DS} = 10V, I _D = 250mA
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	0.6	—	nC	
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	2.7	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _r	—	2.5	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	19	—	ns	
Turn-Off Fall Time	t _f	—	11	—	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

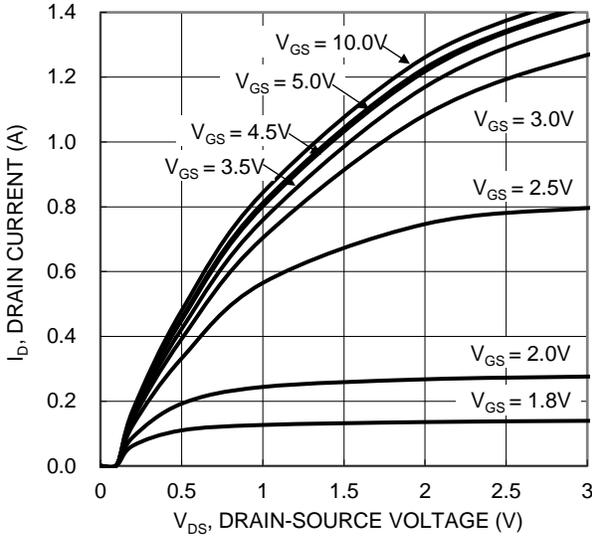


Figure 1. Typical Output Characteristic

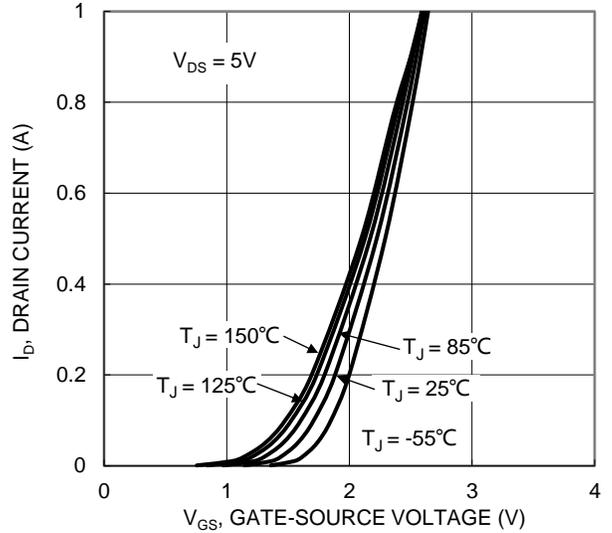


Figure 2. Typical Transfer Characteristic

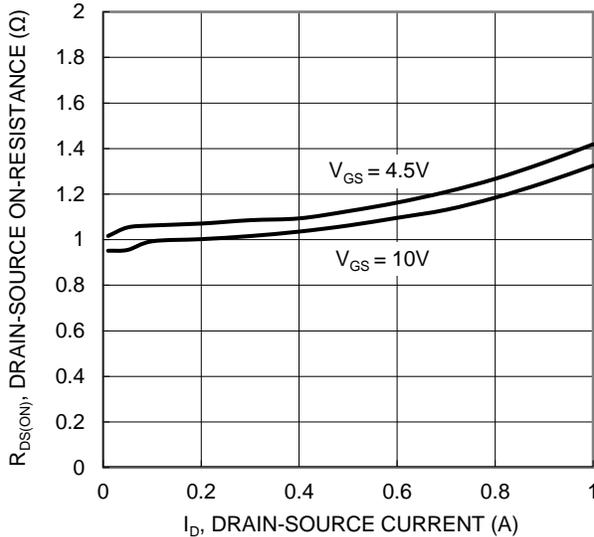


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

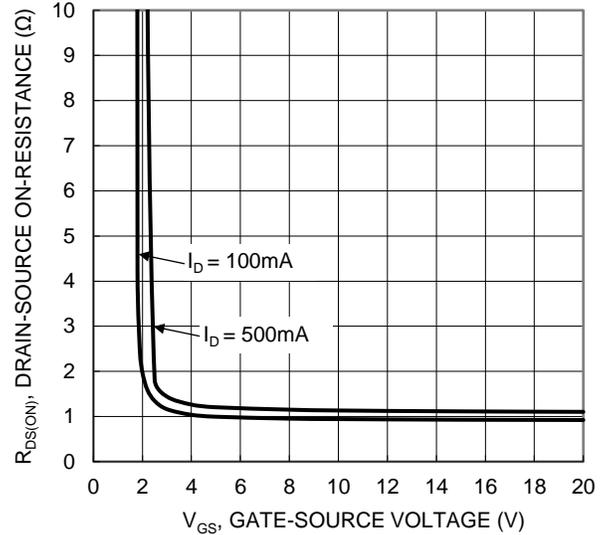


Figure 4. Typical Transfer Characteristic

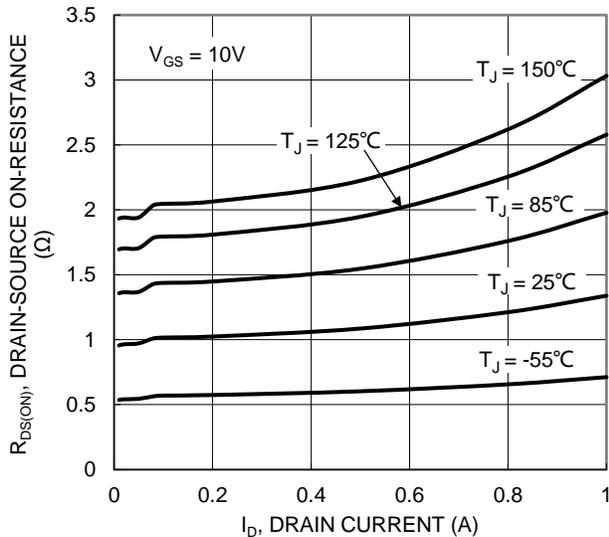


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

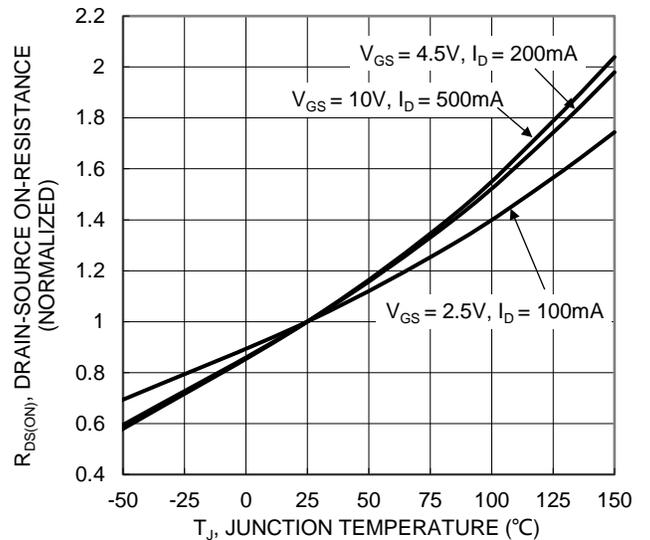


Figure 6. On-Resistance Variation with Temperature

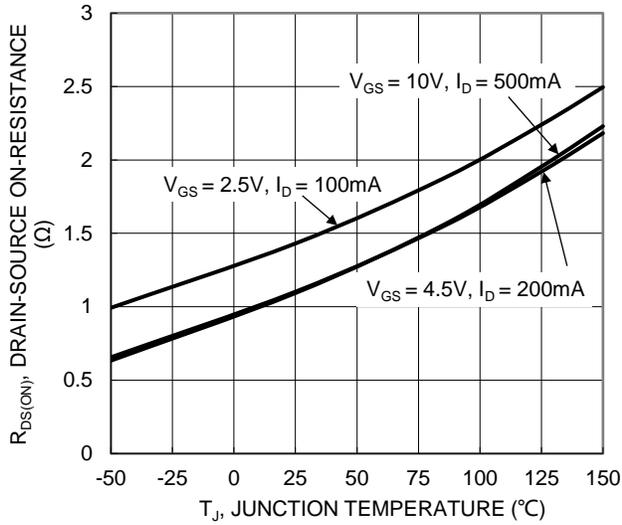


Figure 7. On-Resistance Variation with Temperature

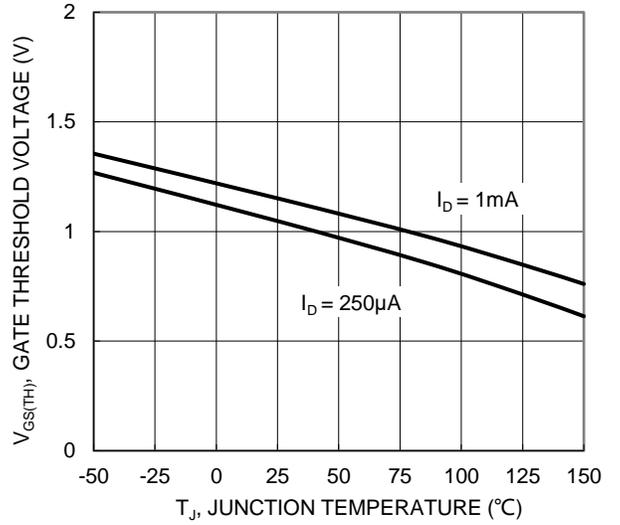


Figure 8. Gate Threshold Variation vs. Junction Temperature

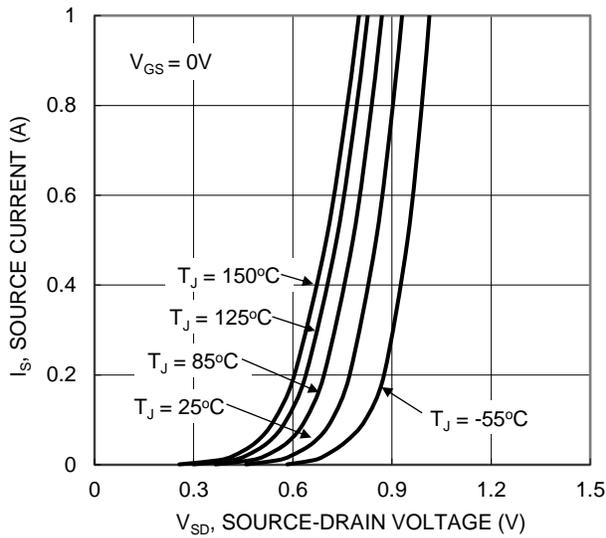


Figure 9. Diode Forward Voltage vs. Current

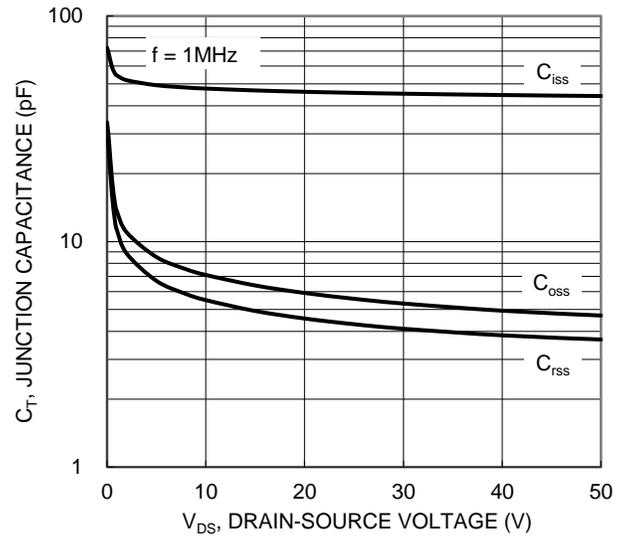


Figure 10. Typical Junction Capacitance

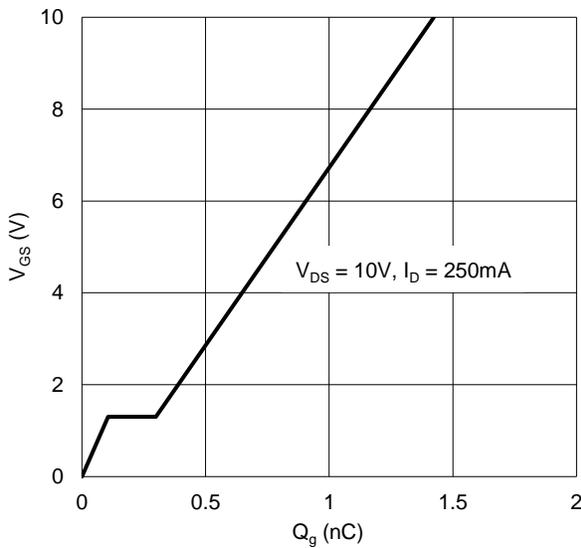


Figure 11. Gate Charge

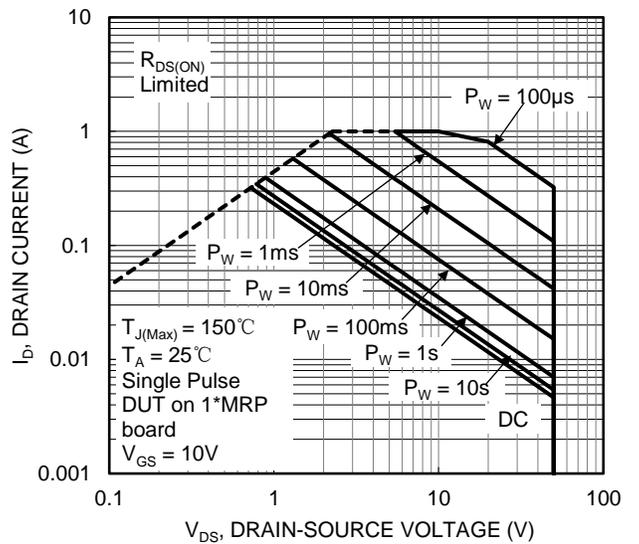


Figure 12. SOA, Safe Operation Area

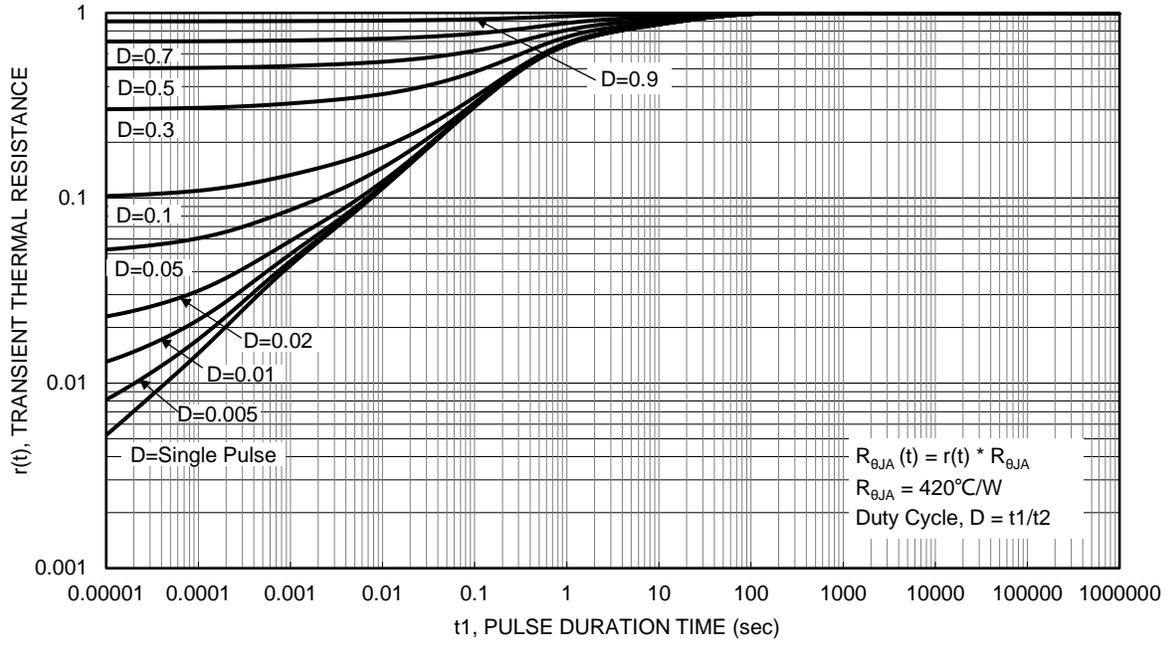
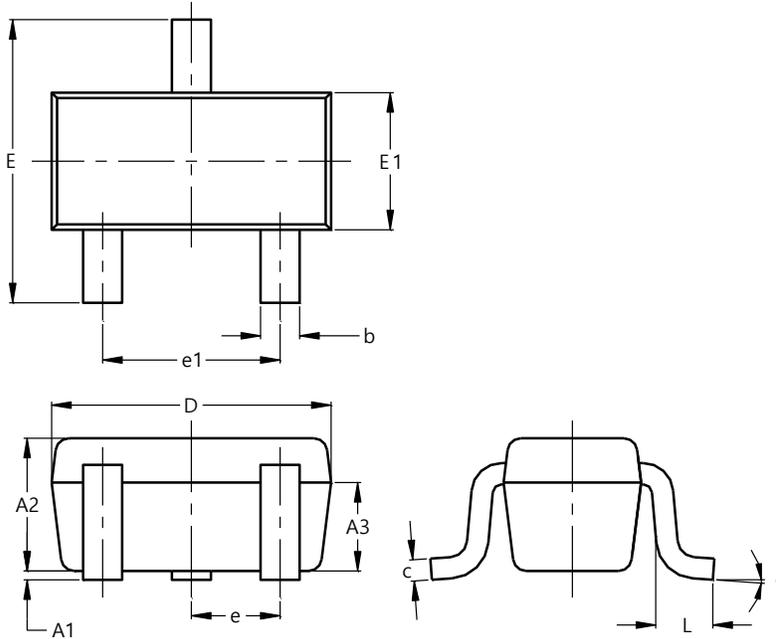


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT523

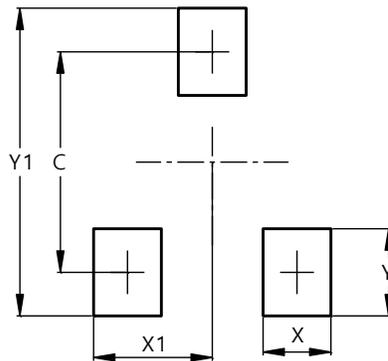


SOT523			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT523



Dimensions	Value (in mm)
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80

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